

# 5DS11M

## Switching Diode



### Features

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- Low-Leakage Diode

Item	Characteristics
Wafer size	5inch
Chip size	280*280um

### Maximum Ratings @25degC

Item	Symbol	Value	Unit
Non-Repetitive Peak Reverse Voltage	VRSM	85	V
Repetitive Peak Reverse Voltage	VRRM	85	V
Repetitive Peak Forward Current	IFRM	500	mA
Continuous Forward Current	IO	215	mA
Non-Repetitive Peak Forward Current @t=1us	IFSM	4.0	A
Power Dissipation	PD	250	mW
Junction Temperature	Tj	150	degC
Storage Temperature	Tstg	-65to+150	degC

### Electrical Characteristics @25degC

Item	Symbol	Min	Max	Unit	Test Condition
Forward Voltage	VF		0.9	V	IF=1mA
			1.0	V	IF=10mA
			1.1	V	IF=50mA
			1.25	V	IF=150mA
Reverse Current	IR		5.0	nA	VR=75V, Tj=25degC
			80.0	nA	VR=75V, Tj=150degC
Capacitance	CT		2.0	pF	VR=0V, f=1MHz
Reverse Recovery Time	trr		3.0	usec	IF=IR=10mA RL=100Ω, irr=1mA

### Wafer Probing Spec @25degC

Symbol	Min	Max	Unit	Test Condition
VF1		850	mV	IF=1mA
VF2		950	mV	IF=10mA
VF3		1	V	IF=50mA
VF4		1.2	V	IF=150mA
IR		2.9	nA	VR=100V
BV	100		V	IR=100uA

### Ordering Information

Chip Type	Chip Thickness	Back Metalization
5DS11MH	230±15um	Au/As-Au (For AgEpoxy/Eutectic)
5DS11MS	180±15um	Au/As (For Eutectic)

### Note

Equivalent type : BAS116

SheetNo.

Rev.